

IN THE CLAIMS:

Kindly amend claims 17 and 19, and add new claims 51-64 as follows:

The present listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-16 have been canceled.

17. (Currently amended) An organic die bonding film having a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher when a semiconductor has been bonded to a support member with said film under conditions of 100-2530°C temperature and pressure of 0.1-30 gf/mm², wherein said film comprises an organic material selected from the group consisting of epoxy resin, silicone resin, acrylic resin and polyimide resin.

18. (Previously presented) A film according to claim 19, having a saturation moisture absorption of 1.0% by volume or less.

19. (Currently amended) An organic die-bonding single layer film having the property of bonding a semiconductor chip to a support member under conditions of 100-2530°C temperature and pressure of 0.1-30 gf/mm², and having a modulus of elasticity of 10 MPa or less at a temperature of 250°C, wherein the film comprises an organic material selected from the group consisting of epoxy resin, silicon resin, acrylic resin, silicone resin and polyimide resin.

20. (Canceled)

21. (Previously presented) A film according to claim 19, having a residual volatile component in an amount of not more than 3.0% by weight.

22. (Previously presented) A film according to claim 21, having water absorption of 1.5% by volume or less.

23. (Previously presented) A film according to claim 17, wherein the film has a modulus of elasticity of 10 Mpa or less at a temperature of 250°C.

24. (Previously presented) A film according to claim 23, having a water absorption of 1.5% by volume or less.

25. (Previously presented) A film according to claim 23, having a residual volatile component in an amount of not more than 3.0% by weight.

26. (Previously presented) A film according to claim 25, having a saturation moisture absorption of 1.0% by volume or less.

27. (Previously presented) A film according to claim 26, having a void volume of 10% or less in terms of voids present in the material and at an interface between said material and a support member at a stage where a semiconductor had been bonded to a support member by said material.

28. (Previously presented) A film according to claim 17, wherein the film has a water absorption of 1.5% by volume or less, a saturation moisture absorption of 1.0% by volume or less, and a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

29. (Previously presented) A film according to claim 17, wherein the film has a saturation moisture absorption of 1.0% by volume or less, and a modulus of elasticity of 10 MPa or less at a temperature of 250°C.

30. (Previously presented) An organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm², wherein the film has a water absorption of 1.5% by volume or less, a saturation moisture absorption of 1.0% by volume or less, a modulus of elasticity of 10 MPa or less at a temperature of 250°C, a void volume of 10% or less in terms of voids present in the film and at an interface between said film and a support member at a stage where a semiconductor has been bonded to a support member by said film, a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher at a stage where a semiconductor has been bonded to a support member with said film, and a residual volatile component in an amount of not more than 3.0% by weight, wherein the film comprises an organic material selected from the group consisting of epoxy resin, silicone resin, acrylic resin and polyimide resin.

31. (Previously presented) A film according to claim 17, wherein the film is a self-supporting film.

32. (Previously presented) A film according to claim 30, wherein the film is a self-supporting film.

33. (Previously presented) A film according to claim 17, wherein the film has a single layer structure.

34. (Previously presented) A film according to claim 30, wherein the film has a single layer structure.

35. (Canceled)

36. (Canceled)

37. (Previously presented) A film according to claim 17, wherein said film comprises a polyimide film.

38. (Previously presented) A film according to claim 30, wherein said film comprises a polyimide resin.

39. (Previously presented) A film according to claim 37, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-dimethylphenyl)methane.

40. (Previously presented) A film according to claim 37, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminodiphenyl ether.

41. (Previously presented) A film according to claim 37, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-diisopropylphenyl)methane.

42. (Previously presented) A film according to claim 37, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

43. (Previously presented) A film according to claim 37, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride), 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

44. (Previously presented) A film according to claim 37, wherein said polyimide is synthesized from 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl] propane.

45. (Previously presented) A film according to claim 17, wherein said film further comprises an epoxy resin.

46. (Previously presented) A film according to claim 30, wherein said film further comprises an epoxy resin.

47. (Previously presented) A film according to claim 17, further comprising a metal filler.

48. (Previously presented) A film according to claim 30, further comprising a metal filler.

49. (Previously presented) A film according to claim 17, made by a process comprising the steps of coating a varnish on a carrier film and peeling the die bonding film from said carrier film.

50. (Previously presented) A film according to claim 30, made by a process comprising the steps of coating a varnish on a carrier film and peeling the die bonding film from said carrier film.

51. (NEW) An organic die bonding film bonding with a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher when a semiconductor has been bonded to a support member with said film under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm², wherein said film comprises an organic material that includes epoxy resin and polyimide resin.

52. (NEW) A film according to claim 51, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-dimethylphenyl)methane.

53. (NEW) A film according to claim 51, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminodiphenyl ether.

54. (NEW) A film according to claim 51, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-diisopropylphenyl)methane.

55. (NEW) A film according to claim 51, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-aminophenoxy)phenyl]propane.

56. (NEW) A film according to claim 51, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride), 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl]propane.

57. (NEW) A film according to claim 51, wherein said polyimide is synthesized from 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl]propane.

58. (NEW) An organic die-bonding single layer film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm², and having a modulus of elasticity of 10 MPa or less at a temperature of 250°C, wherein the film comprises an organic material that includes epoxy resin and polyimide resin.

59. (NEW) A film according to claim 58, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-dimethylphenyl)methane.

60. (NEW) A film according to claim 58, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 4,4'-diaminodiphenyl ether.

61. (NEW) A film according to claim 58, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and bis(4-amino-3,5-diisopropylphenyl)methane.

62. (NEW) A film according to claim 58, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride) and 2,2-bis[4-(4-aminophenoxy)phenyl]propane.

63. (NEW) A film according to claim 58, wherein said polyimide is synthesized from 1,2-(ethylene)bis(trimellitate anhydride), 1,10-(decamethylene)bis(trimellitate anhydride), and 2,2-bis[4-(4-aminophenoxy)phenyl]propane.

64. (NEW) An organic die-bonding film having the property of bonding a semiconductor chip to a support member under conditions of 100-250°C temperature and pressure of 0.1-30 gf/mm², wherein the film has a water absorption of 1.5% by volume or less, a saturation moisture absorption of 1.0% by volume or less, a modulus of elasticity of 10 MPa or less at a temperature of 250°C, a void volume of 10% or less in terms of voids present in the film and at an interface between said film and a support member at a stage where a semiconductor has been bonded to a support member by said film, bonds with a peel strength of 0.5 kgf/(5 mm x 5 mm chip) or higher at a stage where a semiconductor has been bonded to a support member with said film, and a residual volatile component in an amount

of not more than 3.0% by weight, wherein the film comprises an organic material that includes epoxy resin and polyimide resin.